

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	((parquet\$3 near2 (pattern patent)) with (wafer chip ((silicon semiconductor) near substrate) pcb board substrate) with (row with column with (component device)) with (test\$3 near (contact pad)) with rotat\$3). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 13:49
L2	0	("2007/0051984"). URPN.	USPAT	OR	ON	2009/03/01 13:49
L3	1	((parquet\$3 near2 (pattern patent)) same (wafer chip ((silicon semiconductor) near substrate) pcb board substrate) same (row with column with (component device)) same (test\$3 near (contact pad)) same rotat\$3). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 13:50
L4	1	((parquet\$3 near2 (pattern patent)) and (wafer chip ((silicon semiconductor) near substrate) pcb board substrate) and (row with column with (component device)) and (test\$3 near (contact pad)) and rotat\$3). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 13:51
L5	1	((wafer chip ((silicon semiconductor) near substrate) pcb board substrate) with (group\$3 row with column with (component device)) with degree with rotat\$3 with (four near1 (adjacent neighbor))) clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 13:54
L6	1	((wafer chip ((silicon semiconductor) near substrate) pcb board substrate) same (group\$3 row with column with (component device)) same degree same rotat\$3 same (four near1 (adjacent neighbor))) clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 13:55

L7	1	((wafer chip ((silicon semiconductor) near substrate) pcb board substrate) and (group\$3 row with column with (component device)) and degree and rotat\$3 and (four near1 (adjacent neighbor))). cfm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 13:55
L8	0	("2007/0051984").URPN.	USPAT	OR	ON	2009/03/01 13:56
L9	14	US-4467400-\$.DID. OR US-6358776-\$.DID. OR US-6380729-\$.DID. OR US-6686224-\$.DID. OR US-20010042901-\$.DID. OR US-20030141860-\$.DID. OR US-20030237061-\$.DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 13:57
L10	4983	257/48,620,e21.596,e21.599. ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 14:10
L11	6059	438/14,113,460,462.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 14:10
L12	9938	10 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 14:11
L13	13	12 and (wafer chip ((silicon semiconductor) near substrate) pcb board substrate) and (group\$3 row with column with (component chip device)) and degree and rotat\$3 and (four near1 (adjacent neighbor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 14:12
L14	28	12 and (wafer chip ((silicon semiconductor) near substrate) pcb board substrate) and (group\$3 row with column with (component chip device)) and (four near1 (adjacent neighbor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 14:15

L15	15	14 not 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/01 14:15
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